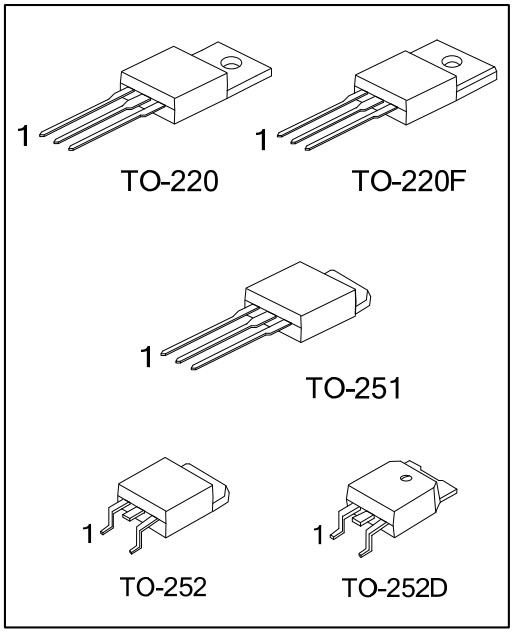
2N90

Power MOSFET

2A, 900V N-CHANNEL POWER MOSFET



■ DESCRIPTION

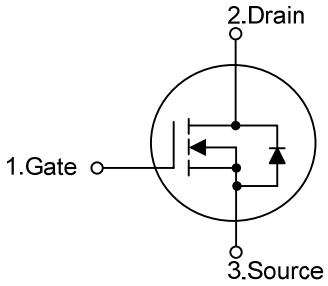
The UTC **2N90** is an N-channel mode power MOSFET using UTC's advanced technology to provide costumers with planar stripe and DMOS technology. This technology specialized in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **2N90** is universally applied in high efficiency switch mode power supply.

■ FEATURES

* $R_{DS(ON)}$ < 7.2Ω @ V_{GS}=10V, I_D=1.1A
* High switching speed
* Improved dv/dt capability
* 100% avalanche tested

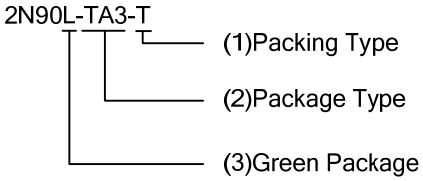
■ SYMBOL



■ ORDERING INFORMATION

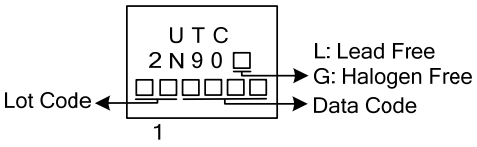
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N90L-TA3-T	2N90G-TA3-T	TO-220	G	D	S	Tube
2N90L-TF3-T	2N90G-TF3-T	TO-220F	G	D	S	Tube
2N90L-TM3-T	2N90G-TM3-T	TO-251	G	D	S	Tube
2N90L-TN3-R	2N90G-TN3-R	TO-252	G	D	S	Tape Reel
2N90L-TND-R	2N90G-TND-R	TO-252D	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF3: TO-220F, TM3: TO-251, TN3: TO-252, TND: TO-252D
(3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage (Note 2)		V_{DSS}	900	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	2.2	A
	Pulsed (Note 2)	I_{DM}	8.8	A
Avalanche Current (Note 2)		I_{AR}	2.2	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	170	mJ
	Repetitive (Note 2)	E_{AR}	8.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.0	V/ns
Power Dissipation	TO-220	P_D	85	W
	TO-220F		25	
	TO-251/ TO-252 TO-252D		43	
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 65mH, I_{AS} = 2.2A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 2.2A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

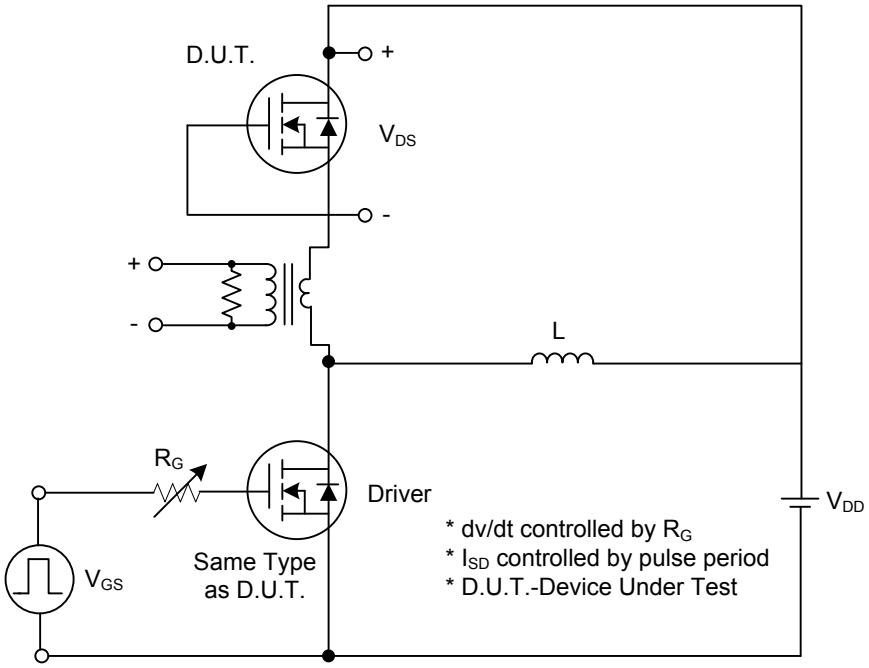
PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	°C/W
	TO-251/ TO-252 TO-252D		110	
Junction to Case	TO-220	θ_{JC}	1.47	°C/W
	TO-220F		5	
	TO-251/ TO-252 TO-252D		2.85	

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

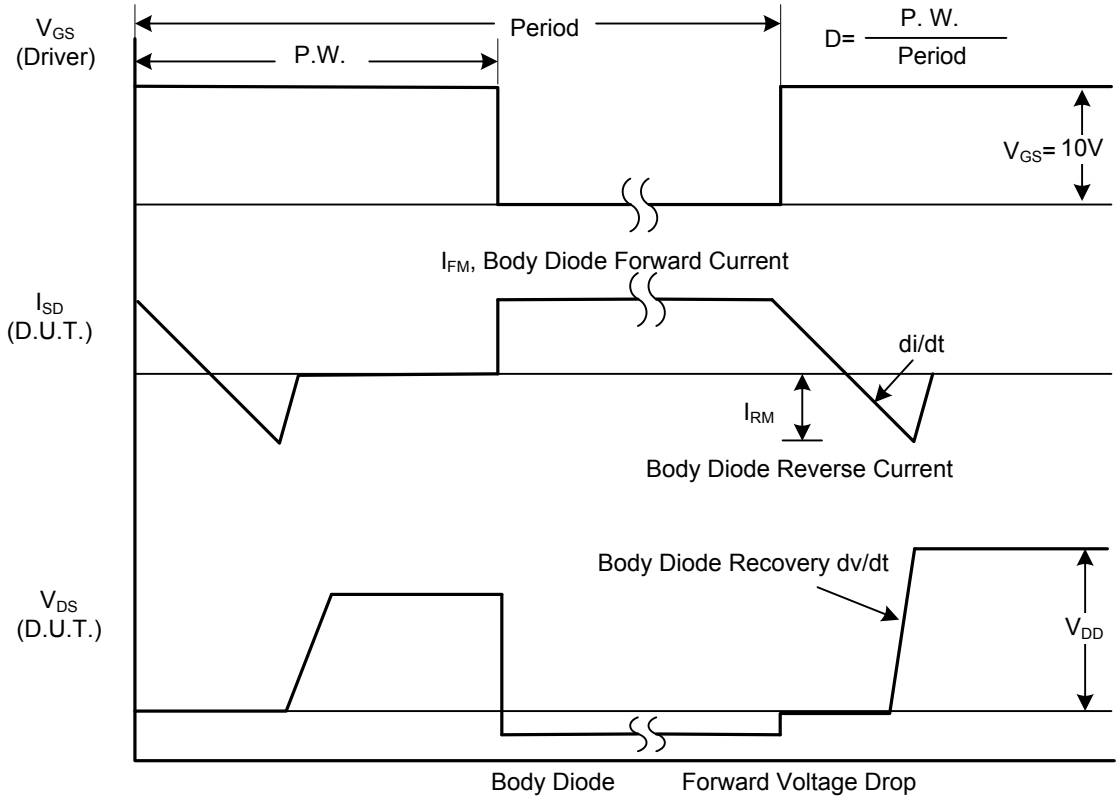
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	900			V
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	Reference to 25°C, I_D=250μA		1.0		V/°C
Drain-Source Leakage Current		I_{DSS}	V_{DS}=900V, V_{GS}=0V			10	μA
			V_{DS}=720V, T_C=125°C			100	
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	3.0		5.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=1.1A		5.6	7.2	Ω
Forward Transconductance		g_{FS}	V_{DS}=50V, I_D=1.1A (Note 1)		2.0		S
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		480	520	pF
Output Capacitance		C_{OSS}			45		pF
Reverse Transfer Capacitance		C_{RSS}			7		pF
SWITCHING PARAMETERS							
Turn-ON Delay Time		$t_{D(ON)}$	V_{GS}=10V, V_{DD}=30V, I_D=0.5A, R_G=25Ω (Note 1,2)		50		ns
Rise Time		t_R			65		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			90		ns
Fall-Time		t_F			45		ns
Total Gate Charge		Q_G	V_{GS}=10V, V_{DS}=50V, I_D=1.3A I_G=100μA (Note 1,2)		16	26	nC
Gate to Source Charge		Q_{GS}			5.5		nC
Gate to Drain Charge		Q_{GD}			4.5		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				2.2	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				8.8	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=2.2A, V_{GS}=0V			1.4	V
Reverse Recovery Time		t_{rr}	I_S=2.2A,V_{GS}=0V,dI_F/dt=100A/μs (Note 1)		400		ns
Reverse Recovery Charge		Q_{RR}			1.6		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

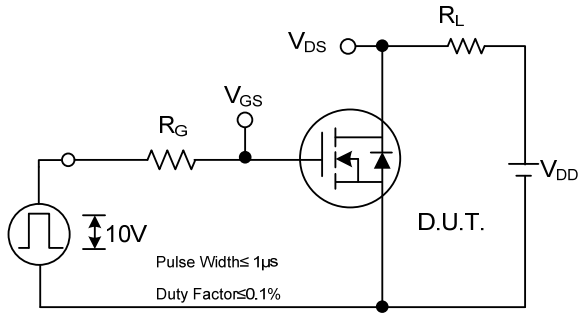


Peak Diode Recovery dv/dt Test Circuit

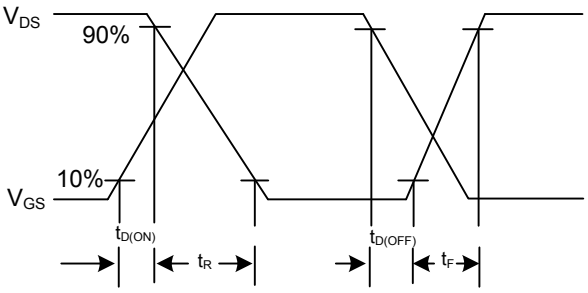


Peak Diode Recovery dv/dt Waveforms

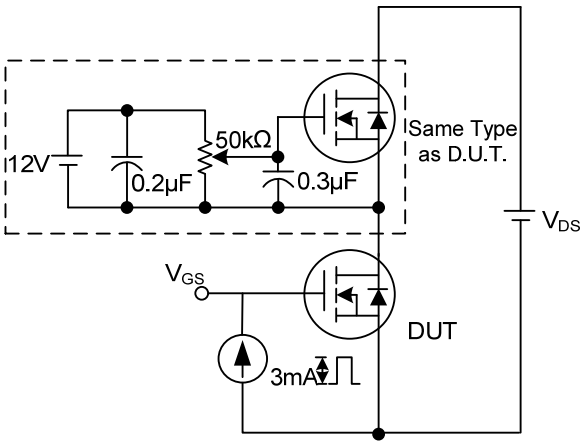
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



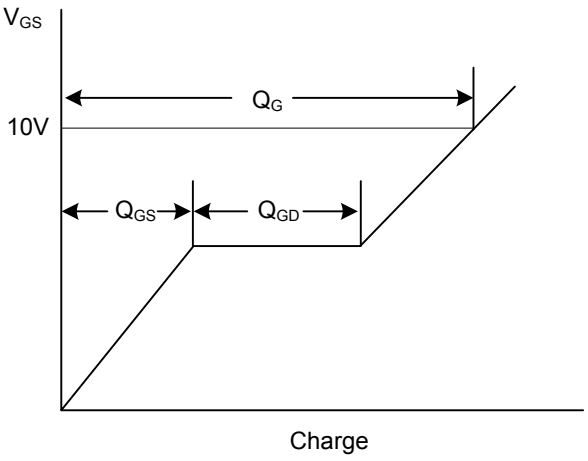
Switching Test Circuit



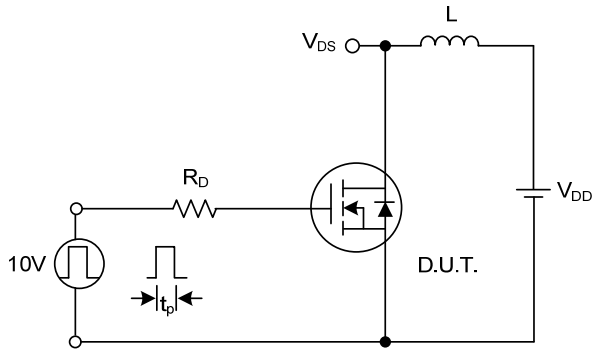
Switching Waveforms



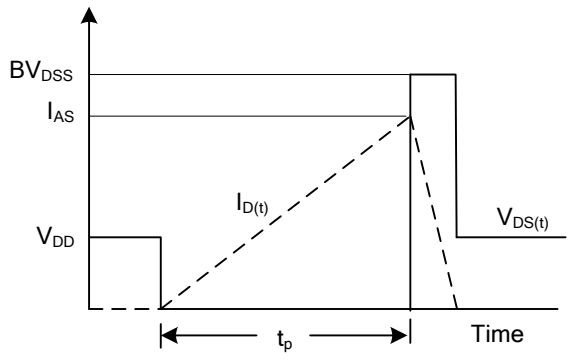
Gate Charge Test Circuit



Gate Charge Waveform



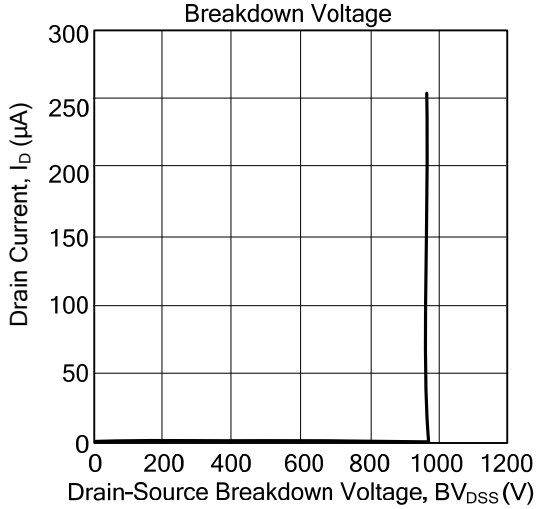
Unclamped Inductive Switching Test Circuit



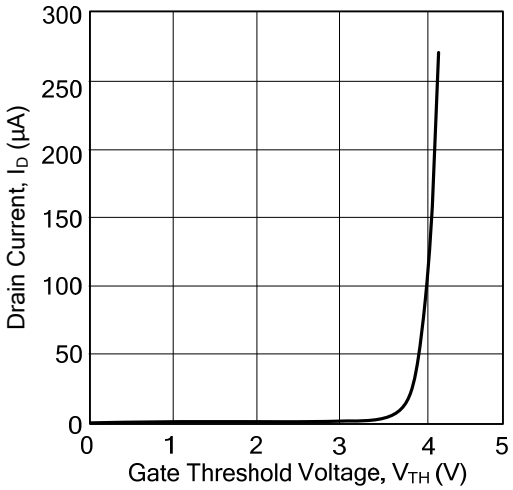
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

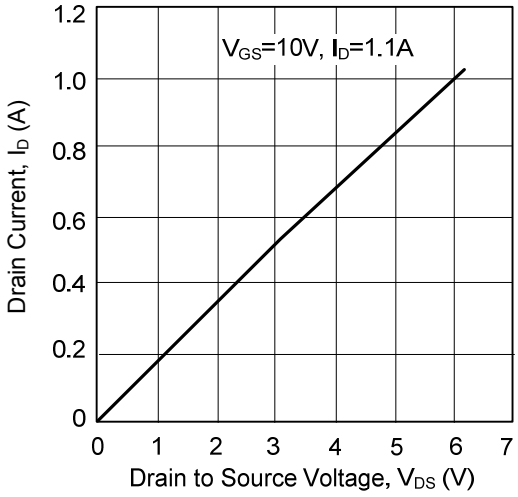
Drain Current vs. Drain-Source Breakdown Voltage



Drain Current vs. Gate Threshold Voltage



Drain-Source On-State Resistance Characteristics



Drain Current vs. Source to Drain Voltage